

XIDER: a novel X-ray detector for
the next generation of high-energy
synchrotron radiation sources

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On behalf of the XIDER collaboration

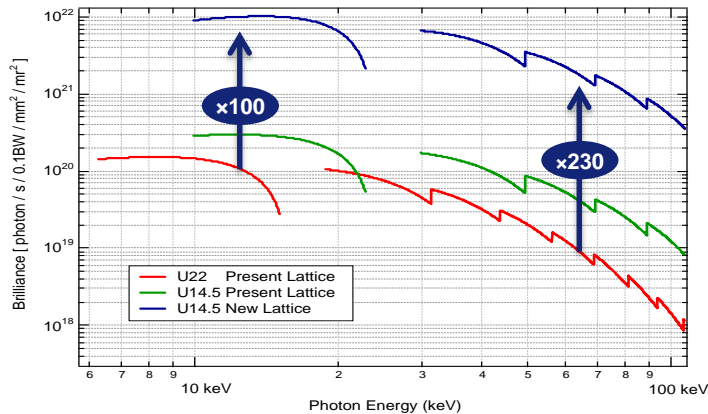
THE 4TH GENERATION SYNCHROTRON CHALLENGES

The Extremely Bright Source (ESRF-EBS)



- First worldwide high-energy 4th generation synchrotron facility. Other facility upgrades ongoing or planned
- Two main challenges:
 1. $\times 100$ more brilliant: **high-flux**
 2. **High-energy** X-rays
- New X-ray instrumentation required to exploit the new source

Brilliance



The XIDER project

- R&D feasibility study (2019-2023)
 - Collaboration with Heidelberg University for microelectronic design

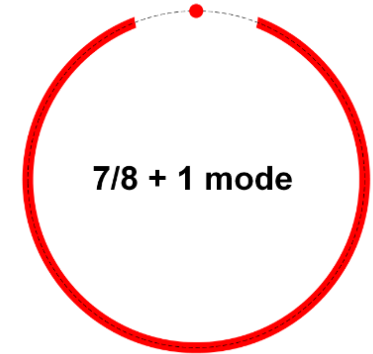


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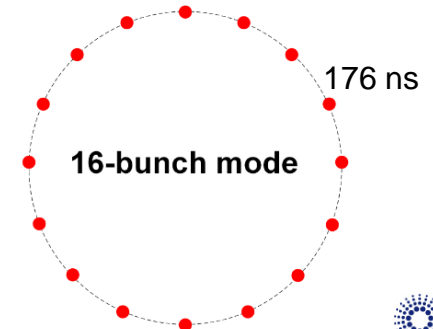
XIDER: Very fast high dynamic range digital integrating detector at **storage rings**

- 2D hybrid pixel detector for **high energy** and **time-resolved** diffraction experiments with ESRF-EBS
- Based on the novel **incremental digital integration** read-out scheme
- Main targets:
 - ✓ Design optimised to operate with high-Z sensors (**30-100 keV**)
 - ✓ 100 μm target pixel pitch (**configurable 2x2 binning**)
 - ✓ High photon fluxes (**up to 10^9** photons/second/pixel)
 - ✓ **Time resolved** capability: burst mode up to 5.68 Mframes/s
 - ✓ High duty cycle, deadtime free readout
 - ✓ **Fully digital** readout

Continuous mode
(high flux)



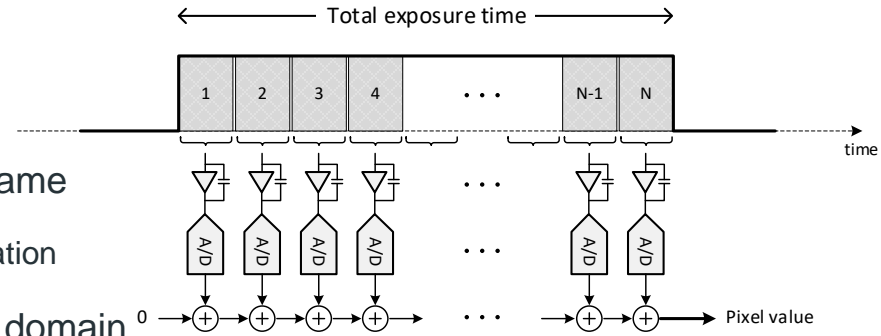
Pulsed mode
(time resolved)



THE INCREMENTAL DIGITAL INTEGRATION

Incremental digital integration:

1. The total exposure time is divided in μs subframes
2. The signal is integrated and digitised for each subframe
 - Noise and leakage are suppressed by signal quantisation
3. The subframe values are accumulated in the digital domain
 - All this processing happens 'in the pixel'



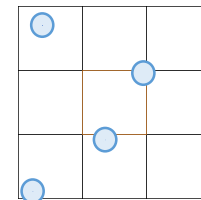
Readout scheme discussed in: *J. Inst.* **15** C01040
<https://doi.org/10.1088/1748-0221/15/01/C01040>

Interesting practical advantages:

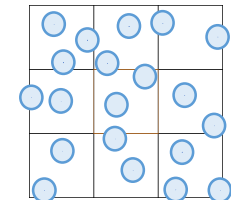
- Suppression of leakage current contributions
- Provides single photon sensitivity
- High dynamic range is achievable
- Fully digital readout
- High resolution ADCs not required

Main challenges of this new readout scheme:

- Minimise the effects of partial charge collection (space and time)
- Combine low-flux and high-flux regimes

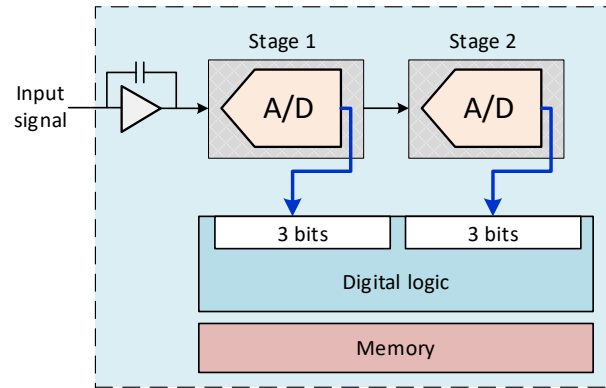
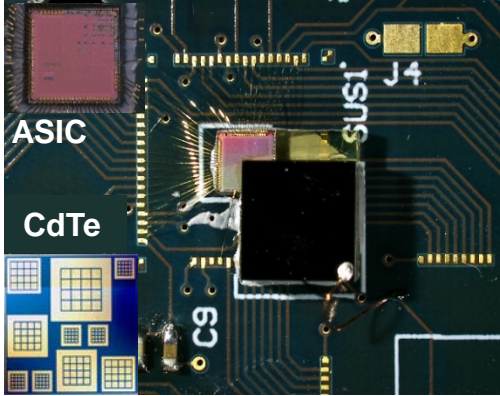


Low flux (PC)

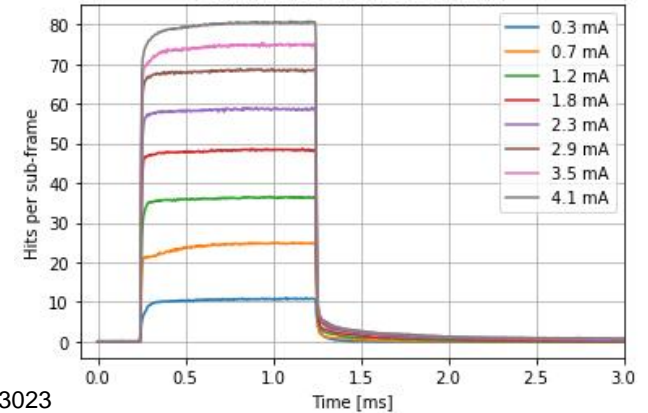


High flux (CI)

CURRENT STATUS OF THE PROJECT



Readout implementation discussed in: *J. Inst.* **16** P03023
<https://doi.org/10.1088/1748-0221/16/03/P03023>



Current work...

- Test sensors: 4 mm × 4 mm CdTe
 - Small pixel matrices of 100, 200 and 300 μm pitch
- Readout chip: TSMC CMOS 65nm
 - 2 stage 3-bit pipelined ADCs in the pixel
- Ongoing characterization
 - “Fighting” with CdTe sensors at high flux
 - Quest for better materials: CZT (?)

...and future plans:

- R&D phase (2019-2023)
- Final specifications defined at the end of the R&D
- Engineering phase planned from 2023